

| | |
|-----------|--------------------------------|
| V_{RRM} | 1200V |
| I_F | 7A ($T_C=161^\circ\text{C}$) |
| Q_C | 31nC |

1200V SILICON CARBIDE
SCHOTTKY DIODE

◆ Features

- Negligible reverse recovery
- High-speed switching
- Positive Temperature Coefficient
- Temperature-Independent Switching
- RoHS compliant



◆ Benefits

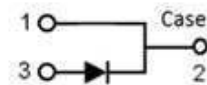
- Higher frequency
- Low heat dissipation requirements
- Reduce size and cost of the system
- High-reliability



TO-220AC

◆ Applications

- Switch mode power supply
- Solar inverter
- Data Center
- Uninterruptible power supply



Maximum Ratings (T_c=25°C unless otherwise noted)

| Symbol | Parameter | | Value | Unit | Note |
|-----------------------------------|---------------------------------------|--|-------------|------------------|----------|
| V _{RRM} | Repetitive peak reverse voltage | | 1200 | V | |
| I _F | Continuous forward current | T _c =25°C | 28 | A | Figure 3 |
| | | T _c =135°C | 13 | A | |
| | | T _c =161°C | 7 | A | |
| I _{FSM} | Non-repetitive forward surge current | T _c =25°C, t _p =10ms, Half sine pulse | 45 | A | |
| | | T _c =110°C, t _p =10ms, Half sine pulse | 35 | A | |
| I _{FRM} | Repetitive Peak Forward Surge Current | T _c =25°C, t _p =10ms, Half sine pulse | 35 | A | |
| | | T _c =110°C, t _p =10ms, Half sine pulse | 30 | A | |
| ∫i ² dt | i ² t value | T _c =25°C, t _p =10ms | 10 | A ² S | |
| | | T _c =110°C, t _p =10ms | 6 | A ² S | |
| P _{tot} | Power Dissipation | T _c =25°C | 174 | W | Figure 4 |
| | | T _c =110°C | 75 | W | |
| | | T _c =150°C | 29 | W | |
| T _j , T _{stg} | Operating and Storage Temperature | | -55 to +175 | °C | |

Electrical Characteristics (T_c=25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Value | | | Unit | Note |
|-----------------|---------------------------|--|-------|------|------|------|----------|
| | | | Min. | Typ. | Max. | | |
| V _{DC} | DC blocking voltage | | 1200 | - | - | V | |
| V _F | Forward voltage | I _F =3.5A | - | 1.2 | - | V | Figure 1 |
| | | I _F =7A, T _c =25°C | - | 1.5 | 1.7 | V | |
| | | I _F =7A, T _c =175°C | - | 2 | - | V | |
| I _R | Reverse current | V _R =1200V, T _c =25°C | - | 2 | 120 | µA | Figure 2 |
| | | V _R =1200V, T _c =175°C | - | 12 | - | µA | |
| Q _C | Total capacitive charge | V _R =800V | - | 31 | - | nC | Figure 6 |
| C | Total capacitance | V _R =1V, f=1MHZ | - | 356 | - | pF | Figure 5 |
| | | V _R =400V, f=1MHZ | - | 26 | - | pF | |
| | | V _R =800V, f=1MHZ | - | 21 | - | pF | |
| E _C | Capacitance Stored Energy | V _R =800V | - | 8.7 | - | µJ | Figure 7 |

Thermal Characteristics

| Symbol | Parameter | Value | | Unit | Note |
|----------------------|---------------------------------------|-------|------|------|----------|
| | | Typ. | Max. | | |
| R _{th(j-c)} | Thermal resistance (Junction to case) | 0.864 | - | °C/W | Figure 8 |

Electrical Characteristic Curves

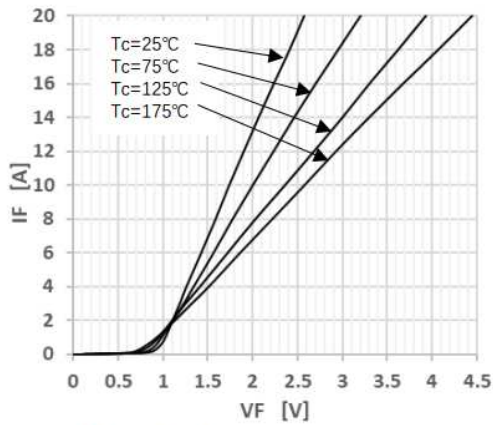


Figure 1 Forward Characteristics

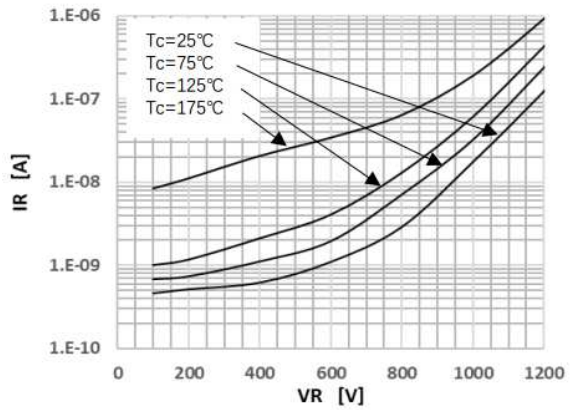


Figure 2 Reverse Characteristics

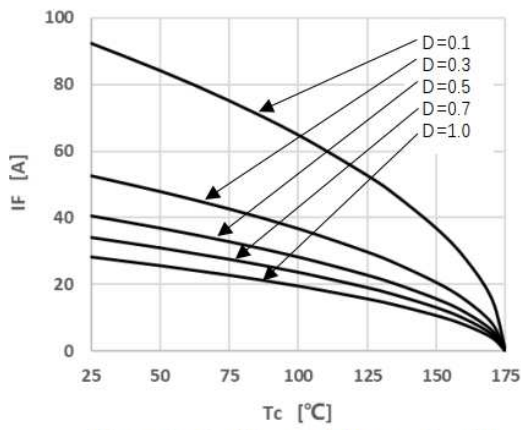


Figure 3 Peak Forward Current Derating

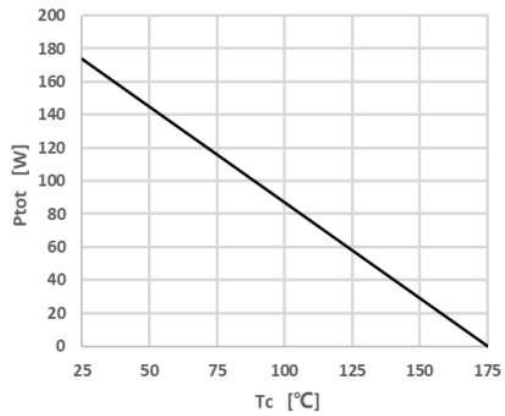


Figure 4 Power Dissipation

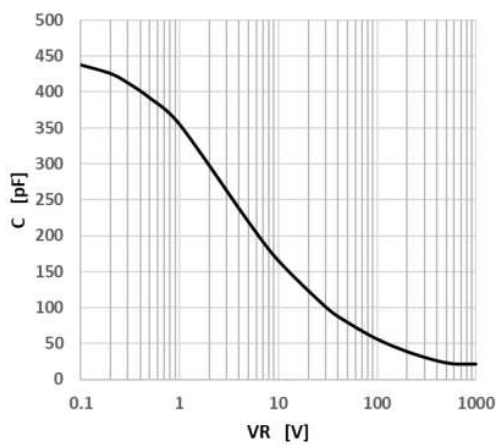


Figure 5 Capacitance vs. Reverse Voltage

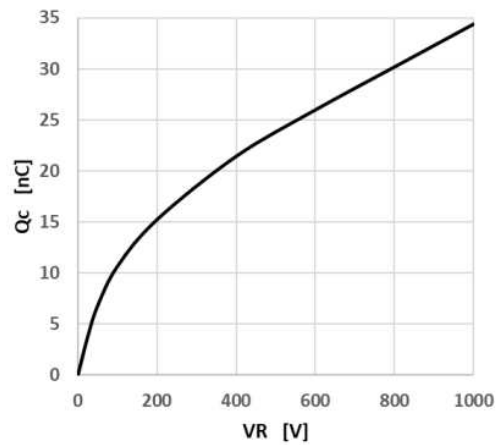


Figure 6 Capacitance Charge vs. Reverse Voltage

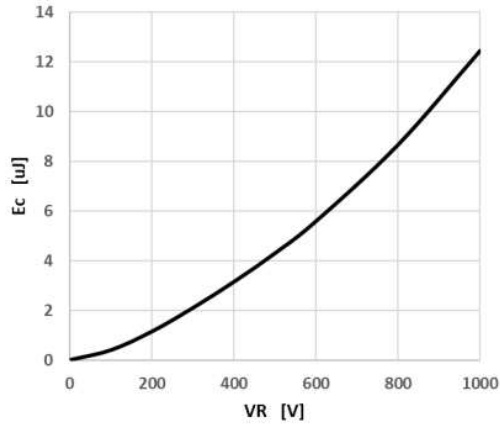


Figure 7 Capacitance Stored Energy

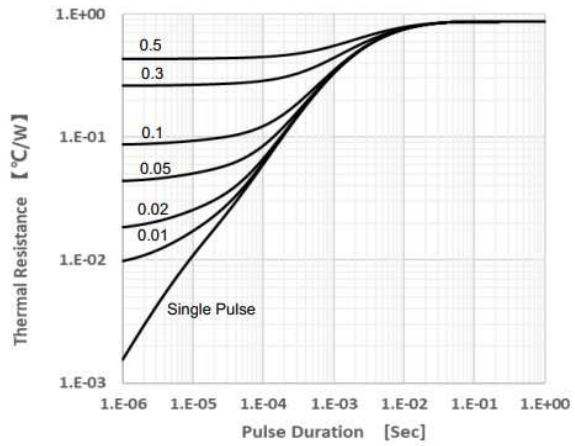
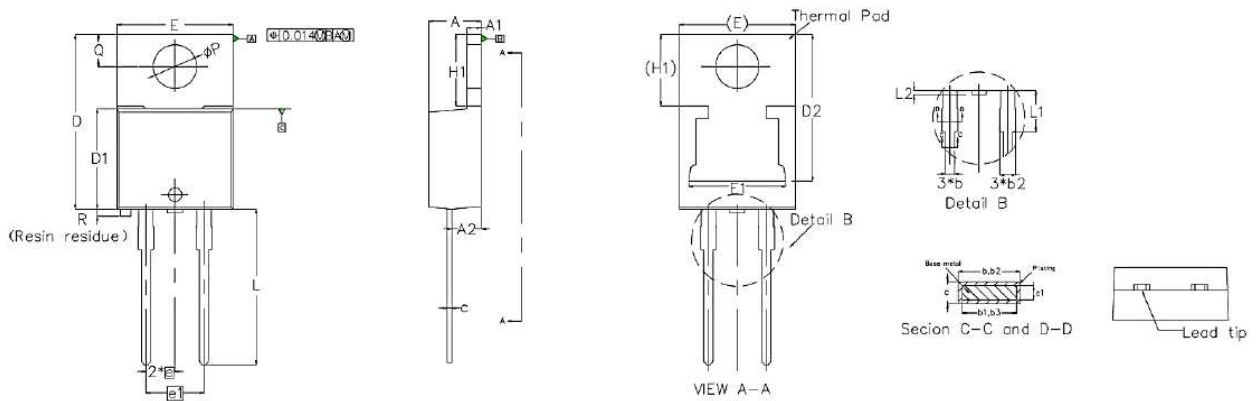


Figure 8 Transient Thermal Impedance

TO-220AC Package Dimensions : (Unit : mm)



| SYMBOL | MILLIMETERS | | | NOTES | SYMBOL | MILLIMETERS | | | NOTES |
|--------|-------------|-------|-------|-------|--------|-------------|-------|-------|-------|
| | Normal | MIN. | MAX. | | | Normal | MIN. | MAX. | |
| A | 4.55 | 4.44 | 4.65 | | E1 | 8.57 | 8.25 | 8.89 | |
| A1 | 1.27 | 1.14 | 1.39 | | e | 2.54 | 2.41 | 2.67 | |
| A2 | 2.60 | 2.54 | 2.79 | | e1 | 5.08 | 4.95 | 5.20 | |
| b | 0.85 | 0.69 | 0.94 | | H1 | 6.20 | 6.09 | 6.40 | |
| b1 | 0.83 | 0.38 | 0.97 | | L | 13.60 | 13.52 | 14.00 | |
| b2 | 1.33 | 1.20 | 1.45 | | L1 | 3.60 | 3.56 | 3.80 | |
| b3 | 1.33 | 1.20 | 1.45 | | L2 | - | 0 | 0.35 | |
| c | 0.50 | 0.36 | 0.56 | | φP | 3.80 | 3.70 | 3.91 | |
| c1 | 0.48 | 0.36 | 0.56 | | Q | 2.80 | 2.62 | 2.87 | |
| D | 15.25 | 14.95 | 15.32 | | R | | | 0.2 | |
| D1 | 8.75 | 8.50 | 8.89 | | | | | | |
| D2 | 12.85 | 12.20 | 13.30 | | | | | | |
| E | 10.18 | 10.11 | 10.40 | | | | | | |

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